Abstracts

Extrinsic elements extraction of DGMESFET

Wei-Kung Deng and Tah-Hsiung Chu. "Extrinsic elements extraction of DGMESFET." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 157-160.

A procedure for the extraction of extrinsic elements of dual-gate MESFET (DGMESFET) is described in this paper. It is the first time to accurately extract the extrinsic elements of series resistance by considering the distributed channel resistance under the regions of two gates with the use of the "end resistance measurement" method. The extrinsic elements of capacitance and inductance are extracted by three-port Y-matrix and Z-matrix calculation from cold measurements. The developed procedure is useful for the characterization of DGMESFET.

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